

# N-channel TrenchMOS logic level FET Rev. 03 — 19 April 2011

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

#### 1.3 Applications

Automotive and general purpose power switching

#### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C	-	-	75	А
P <sub>tot</sub>	total power dissipation		-	-	230	W
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	4.3	5	mΩ
		$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	3.9	4.6	mΩ
Avalanch	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 25 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 5  \text{V}; \\ T_{\text{j(init)}} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split}$	-	-	500	mJ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

### 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9605-30A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-10	10	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C	-	75	А
		T <sub>mb</sub> = 25 °C	-	75	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed	-	400	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	230	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; t <sub>p</sub> ≤ 50 µs	-15	15	V
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	75	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	240	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 25$ V; $R_{GS} = 50 \Omega$ ; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped	-	500	mJ

# BUK9605-30A

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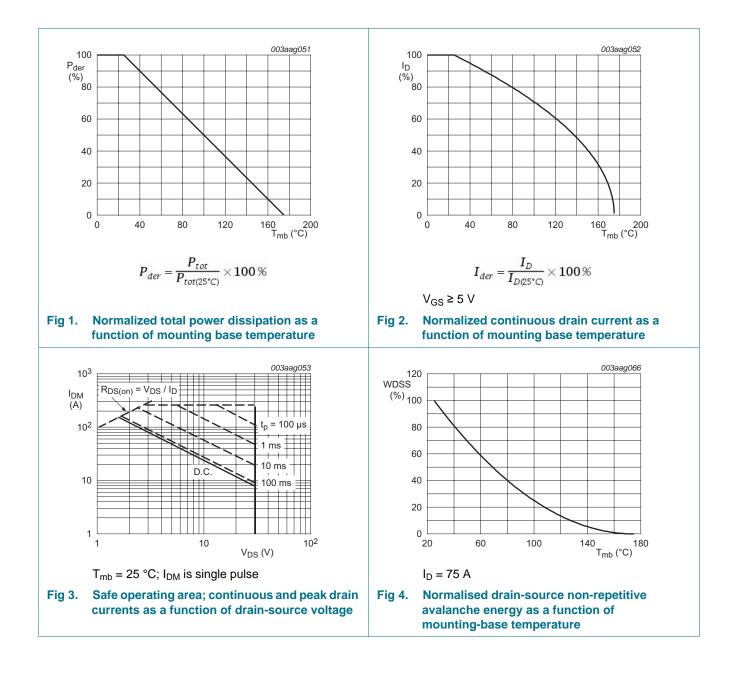


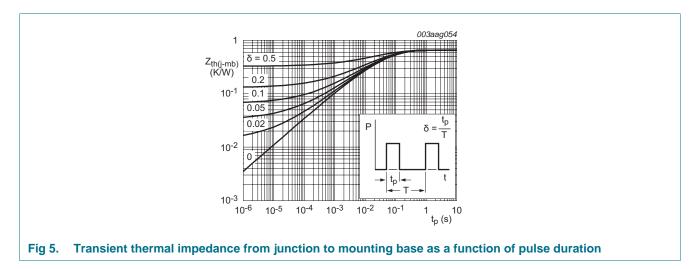
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### 5. Thermal characteristics

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Table 5.	I nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.65	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint ; FR4 board	-	50	-	K/W



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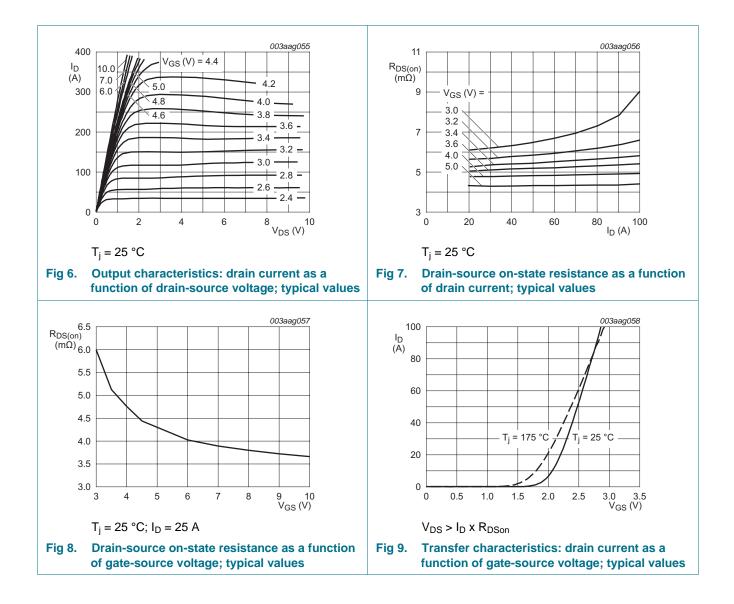
### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub> drain-	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	30	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
	N	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	4.3	5	mΩ
	resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	3.9	4.6	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	5.4	mΩ
		$V_{GS}$ = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C	-	-	9.3	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V$ ; $V_{DS} = 25 V$ ; f = 1 MHz; T <sub>j</sub> = 25 °C	-	6500	8600	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 V$ ; $V_{DS} = 25 V$ ; f = 1 MHz; T <sub>j</sub> = nk °C	-	1500	1800	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	1000	1350	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	45	65	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	220	330	ns
t <sub>d(off)</sub>	turn-off delay time		-	435	600	ns
t <sub>f</sub>	fall time		-	320	450	ns
L <sub>D</sub>	internal drain inductance	measured from upper edge of drain tab to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead soldering point to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-di	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.85	1.2	V
		I <sub>S</sub> = 75 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	1.1	-	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 75 A; dI <sub>S</sub> /dt = -100 A/µs;	-	400	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	1	-	μC
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BUK9605-30A Product data sheet

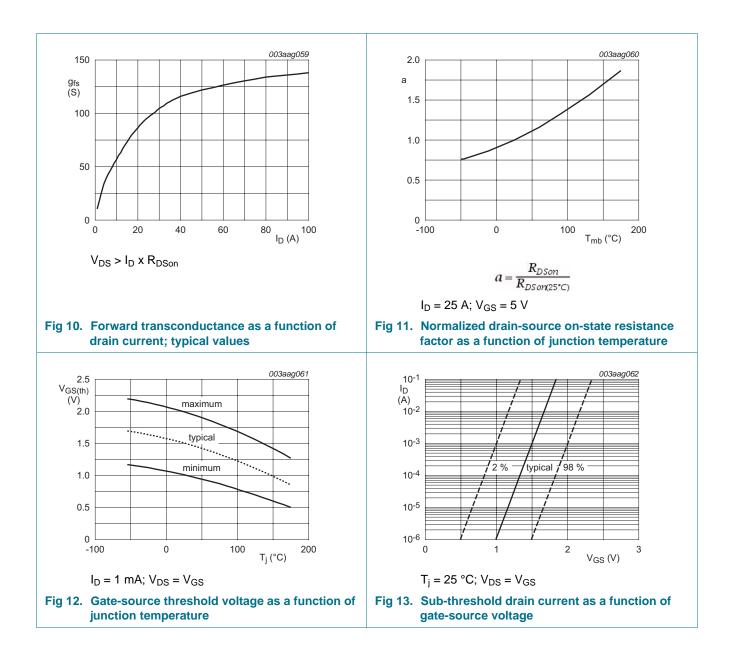
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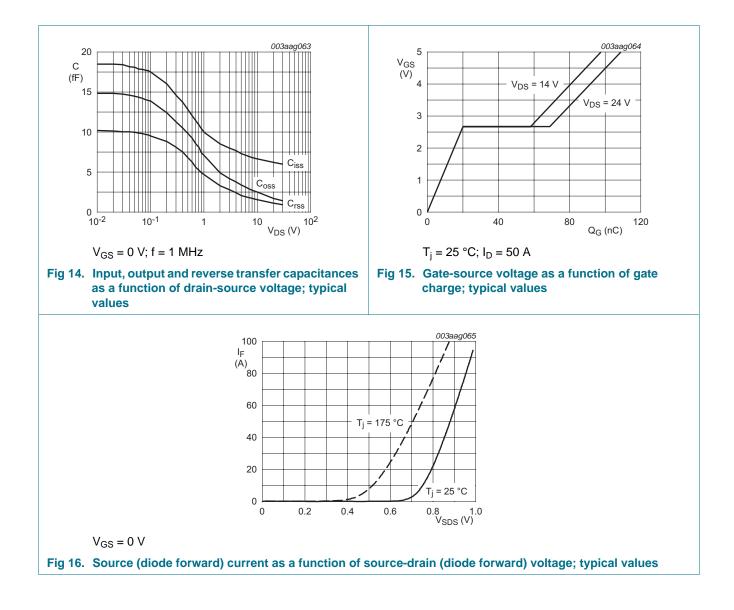
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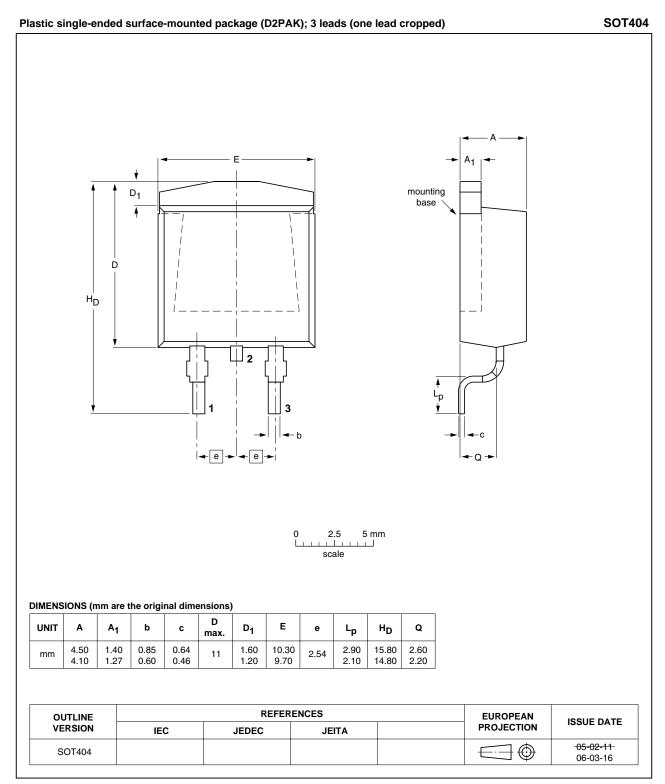
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### 7. Package outline



#### Fig 17. Package outline SOT404 (D2PAK)

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## 8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9605-30A v.3	20110419	Product data sheet	-	BUK9605-30A v.2
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>	this data sheet has been rec conductors.	lesigned to comply with	n the new identity guidelines
	<ul> <li>Legal texts had</li> </ul>	we been adapted to the new	company name where	appropriate.
BUK9605-30A v.2	19990801	Product specification	-	BUK9605-30A v.1

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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